

1c971 U.S. PTO
09/820072
03/28/01

Form PTO-1449 Department of Commerce Patent and Trademark Office		Docket No. PAT004		Serial No. Unassigned		
INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION (Use several sheets if necessary)		Applicants Wen-Yen Hwang				
		Filing Date Herewith		Group Art Unit Unassigned		
U.S. PATENT DOCUMENTS						
*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
JN	5,285,086	02/08/94	Fitzgerald, Jr.			
	5,294,808	03/15/94	Lo			
	5,513,204	04/30/96	Jayaraman			
	5,719,894	02/17/98	Jewell <i>et al.</i>			
	5,754,578	5/19/98	Jayaraman			
	5,914,976	6/22/99	Jayaraman <i>et al.</i>			
	5,981,400	11/09/99	Lo			
FOREIGN PATENT DOCUMENTS						
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
						
						
						
						
OTHER (Including Author, Title, Date, Pertinent Pages, Etc.)						
JN	Matthews, J. W. and Blakeslee, A. E., "Defects in Epitaxial Multilayers," <i>Journal of Crystal Growth</i> 27, (1974), pp. 118-125.					
	Parillaud <i>et al.</i> , "High Quality InP on Si by Conformal Growth," <i>Appl. Phys. Lett.</i> 68, (1996), p. 2654.					
	Lo, Yu-Hwa, "Long Wavelength Vertical Cavity Surface Emitting Lasers," <i>Hot Topic</i> , February 1995, p. 20-21.					
EXAMINER JOSEPH NGUYEN				DATE CONSIDERED 10/1/02		
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.						

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JN	Qian <i>et al.</i> , "1.3 μ m Vertical-Cavity Surface-Emitting Lasers with Double-Bonded GaAs-AlAs Bragg Mirrors," <i>IEEE Photonics Technology Letters</i> , Vol. 9, No. 1, January 1997, pp. 8-10. ✓					
	Uchiyam <i>et al.</i> , "Continuous-Wave Operation up to 36°C of 1.3 μ m GaInAsP-InP Vertical-Cavity Surface-Emitting Lasers," <i>IEEE Photonics Technology Letters</i> , Vol. 9, No. 2, February 1997, pp. 141-142. ✓					
	Dudley, <i>et al.</i> , "Low Threshold, Wafer Fused Long Wavelength Vertical Cavity Lasers," <i>Appl. Phys. Lett.</i> 64 (12), March 1994, pp. 1463-1465. ✓					
	Xiong, Yanyan and Lo, Yu-Hwa, "Current Spreading and Carrier Diffusion in Long-Wavelength Vertical-Cavity Surface-Emitting Lasers," <i>IEEE Photonics Technology Letters</i> , Vol. 10, No. 9, September 1998, pp. 1202-1204. ✓					
	Salet <i>et al.</i> , "Undercut Ridge Structures: A Novel Approach to 1.3/1.55 μ m Vertical-Cavity Lasers Designed for Continuous-Wave Operation," <i>IEEE Proc.-Optoelectron.</i> , Vol. 145, No. 2, April 1998, pp. 125-131. ✓					
	Salet <i>et al.</i> , "Room-Temperature Pulsed Operation of 1.3 μ m Vertical-Cavity Lasers Including Bottom InGaAsP/InP Multilayer Bragg Mirrors," <i>Electronics Letters.</i> , Vol. 33, No. 24, November 1997, pp. 2048-2049. ✓					
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OTHER (Including Author, Title, Date, Pertinent Pages, Etc.)						
JN	Salet <i>et al.</i> , "Gas-Source Molecular-Beam Epitaxy and Optical Characterisation of Highly-Reflective InGaAsP/InP Multilayer Bragg Mirrors for 1.3 μ m Vertical-Cavity Lasers," <i>Electronics Letters</i> , Vol. 33, No. 13, June 1997, pp. 1145-1147.					
I	Qian, <i>et al.</i> , "Submilliamp 1.3 μ m Vertical-Cavity Surface-Emitting Lasers With Threshold Current Density of <500A/cm ² ," <i>Electronics Letters</i> , Vol. 33, No. 12, June 1997, pp. 1052-1054. ✓					
EXAMINER	JOSEPH NGUYEN			DATE CONSIDERED 6/1/02		
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